P&S Processing-in-Memory

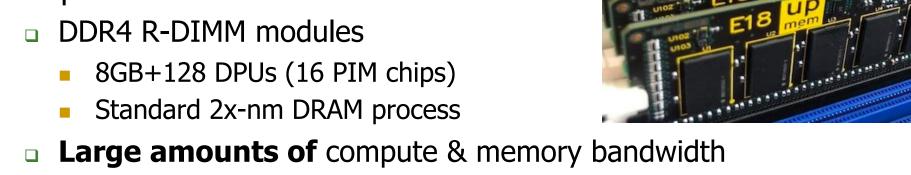
Real-World Processing-in-Memory Architectures: SK Hynix Accelerator-in-Memory

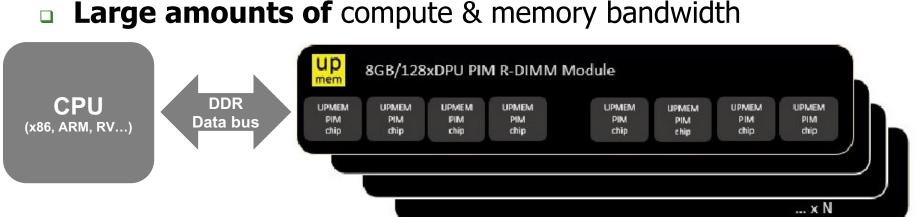
Dr. Juan Gómez Luna Prof. Onur Mutlu ETH Zürich Spring 2022

14 April 2022

UPMEM Processing-in-DRAM Engine (2019)

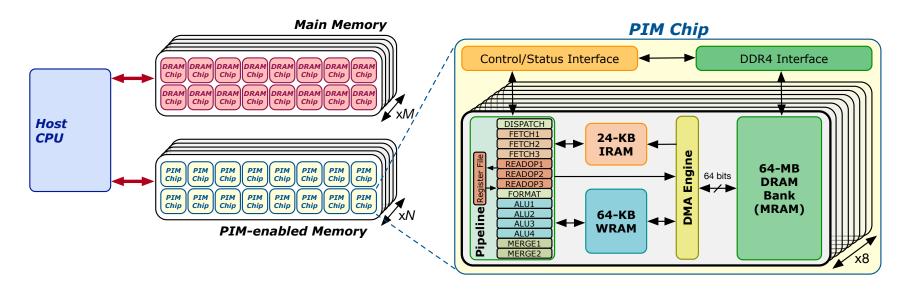
- Processing in DRAM Engine
- Includes standard DIMM modules, with a large number of DPU processors combined with DRAM chips.
- Replaces standard DIMMs





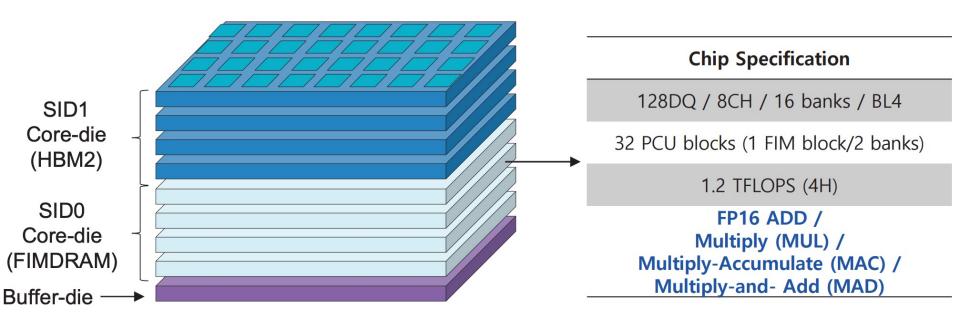
Recall: UPMEM PIM System Organization

- A UPMEM DIMM contains 8 or 16 chips
 - Thus, 1 or 2 ranks of 8 chips each
- Inside each PIM chip there are:
 - 8 64MB banks per chip: Main RAM (MRAM) banks
 - 8 DRAM Processing Units (DPUs) in each chip, 64 DPUs per rank



FIMDRAM: Chip Structure

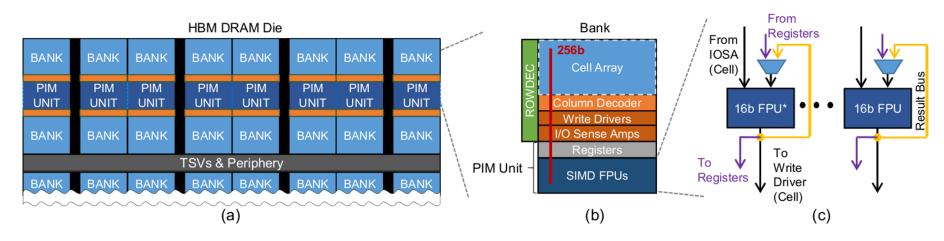
FIMDRAM based on HBM2



[3D Chip Structure of HBM with FIMDRAM]

FIMDRAM: System Organization (III)

- PIM units respond to standard DRAM column commands (RD or WR)
 - Compliant with unmodified JEDEC controllers
- They execute one wide-SIMD operation commanded by a PIM instruction with deterministic latency in a lock-step manner
- A PIM unit can get 16 16-bit operands from IOSAs, a register, and/or the result bus



SK Hynix Accelerator-in-Memory

SK Hynix Accelerator-in-Memory (2022)





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SK hynix Develops PIM, Next-Generation AI Accelerator

February 16, 2022







Seoul, February 16, 2022

SK hynix (or "the Company", www.skhynix.com) announced on February 16 that it has developed PIM*, a nextgeneration memory chip with computing capabilities.

*PIM(Processing In Memory): A next-generation technology that provides a solution for data congestion issues for AI and big data by adding computational functions to semiconductor memory

It has been generally accepted that memory chips store data and CPU or GPU, like human brain, process data. SK hynix, following its challenge to such notion and efforts to pursue innovation in the next-generation smart memory, has found a breakthrough solution with the development of the latest technology.

SK hynix plans to showcase its PIM development at the world's most prestigious semiconductor conference, 2022 ISSCC*, in San Francisco at the end of this month. The company expects continued efforts for innovation of this technology to bring the memory-centric computing, in which semiconductor memory plays a central role, a step closer in Paper 11.1. SK Hynix describes an Tynm, GDDR6-based accelerator-in-memory with a command set for deep-learning operation. The to the reality in devices such as smartphones.

*ISSCC: The International Solid-State Circuits Conference will be held virtually from Feb. 20 to Feb. 24 this year with a theme of "Intelligent Silicon for a Sustainable World"

For the first product that adopts the PIM technology, SK hynix has developed a sample of GDDR6-AiM (Accelerator* in memory). The GDDR6-AiM adds computational functions to GDDR6* memory chips, which process data at 16Gbps. A combination of GDDR6-AiM with CPU or GPU instead of a typical DRAM makes certain computation speed 16 times faster. GDDR6-AiM is widely expected to be adopted for machine learning, high-performance computing, and big data computation and storage



11.1 A 1ynm 1.25V 8Gb, 16Gb/s/pin GDDR6-based Accelerator-in-Memory supporting 1TFLOPS MAC Operation and Various Activation Functions for Deep-Learning Applications

Seongiu Lee, SK hynix, Icheon, Korea

8Gb design achieves a peak throughput of 1TFLOPS with 1GHz MAC operations and supports major activation functions to improve

Accelerator-in-Memory (ISSCC 2022)

ISSCC 2022 / SESSION 11 / COMPUTE-IN-MEMORY AND

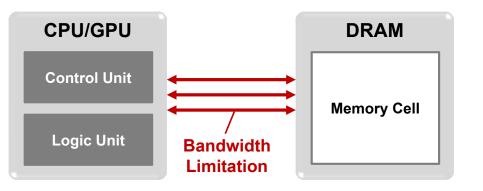
11.1 A 1ynm 1.25V 8Gb, 16Gb/s/pin GDDR6-based Accelerator-in-Memory supporting 1TFLOPS MAC Operation and Various Activation Functions for Deep-Learning Applications

Seongju Lee, Kyuyoung Kim, Sanghoon Oh, Joonhong Park, Gimoon Hong, Dongyoon Ka, Kyudong Hwang, Jeongje Park, Kyeongpil Kang, Jungyeon Kim, Junyeol Jeon, Nahsung Kim, Yongkee Kwon, Kornijcuk Vladimir, Woojae Shin, Jongsoon Won, Minkyu Lee, Hyunha Joo, Haerang Choi, Jaewook Lee, Donguc Ko, Younggun Jun, Keewon Cho, Ilwoong Kim, Choungki Song, Chunseok Jeong, Daehan Kwon, Jieun Jang, Il Park, Junhyun Chun, Joohwan Cho

SK hynix, Icheon, Korea

AiM: Exploiting Bank Parallelism

Memory bandwidth is not enough for many ML workloads



CPU/GPU

Control Unit

Logic Unit

Large Internal

Bandwidth

Processor-centric system

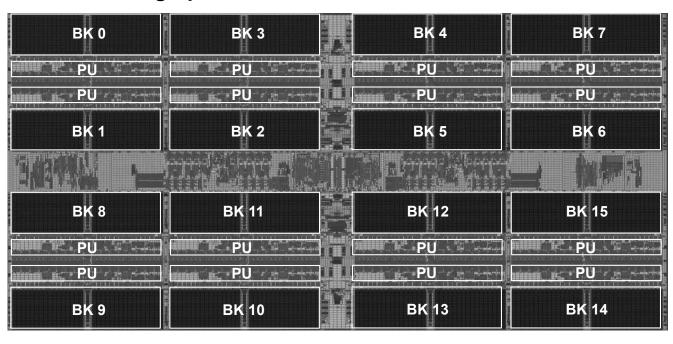
Sy-Memory-centricesystemPIM

Onur Mutlu, "Memory-Centric Computing", Keynote Talk at the Thoughtworks Engineering for Research Symposium (E4R), Virtual, 19 February 2022.

AiM: Chip Implementation

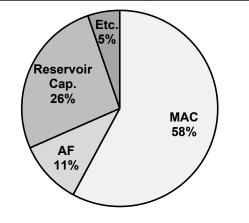
4 Gb AiM die with 16 processing units (PUs)

AiM Die Photograph



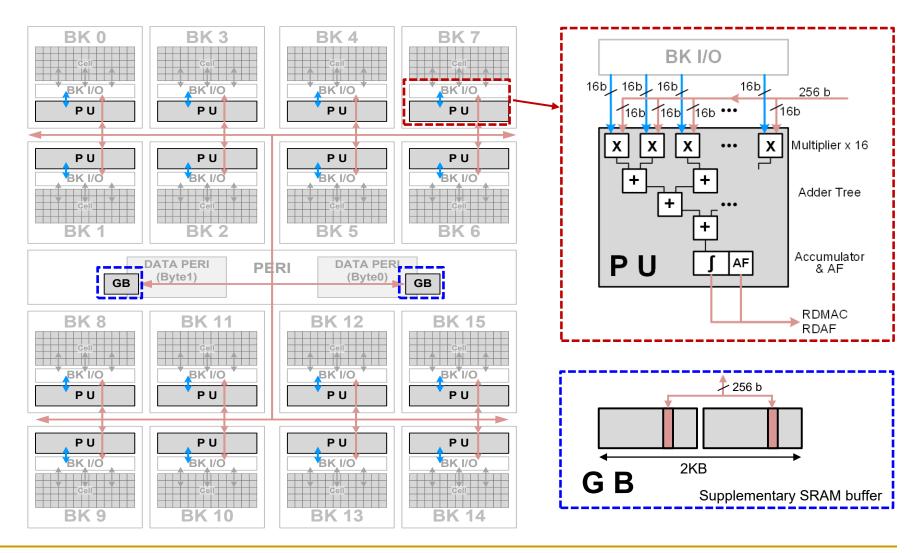
1 Process Unit (PU) Area

Total	0.19mm ²
MAC	0.11mm ²
Activation Function (AF)	0.02mm ²
Reservoir Cap.	0.05mm ²
Etc.	0.01mm ²



AiM: System Organization

GDDR6-based AiM architecture



AiM Commands

AiM: Command Set

New commands for computation

Туре	CMD	Description
	ACT4, ACT16	Activate four/sixteen banks in parallel
Bank Activation	ACTAF4, ACTAF16	Activate rows storing activation function LUTs in four/sixteen banks in parallel
	MACSB, MAC4B, MACAB	Perform MAC in one/four/sixteen banks in parallel
Compute	AF	Compute activation function in all banks
	EWMUL	Perform element-wise multiplication
	WRBK	Write to all activated banks in parallel
	WRGB	Write to Global Buffer
	RDMAC	Read from MAC result register
Data	RDAF	Read from activation function result register
	WRBIAS	Write bias to MAC result register
	RDCP	Copy data from a bank to Global Buffer
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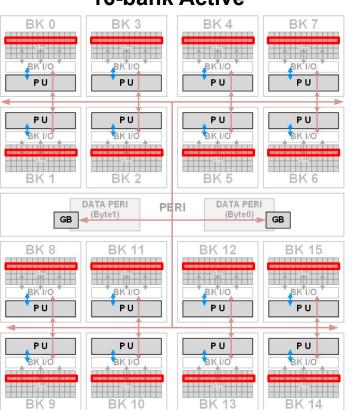
AiM: Command Set: ACT4, ACT16

Activate 4 or 16 banks at once

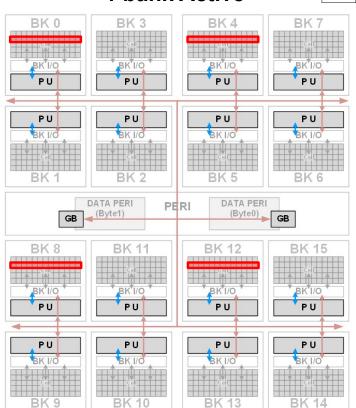
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Activated Word Line

16-bank Active



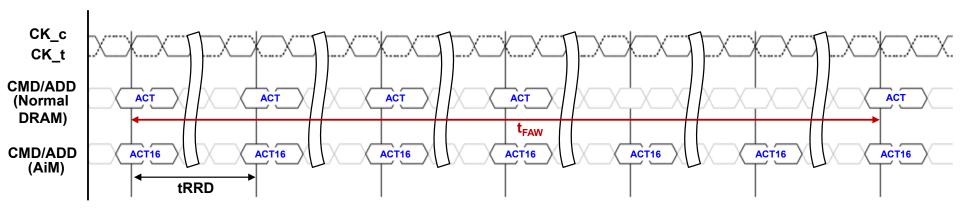
4-bank Active



AiM: Four Active Window (t_{FAW})

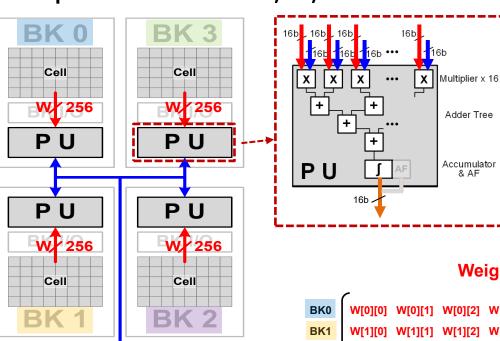
- ACT16 operations are possible without t_{FAW} constraint
 - In normal DRAM only 4 ACT are possible every t_{FAW}
 - Reservoir capacitor in each PU

Туре	CMD	Description
Type	CWID	Description
Bank	ACT4, ACT16	Activate four/sixteen banks in parallel
Activation	ACTAF4, ACTAF16	Activate rows storing activation function LUTs in four/sixteen banks in parallel
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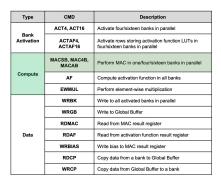
AiM: MAC Operation with Global Buffer

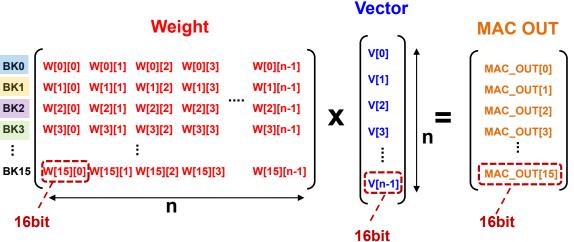
- MAC operation: Weights from the banks, vectors from the GB
- Operates with 16, 4, or 1 PU



256

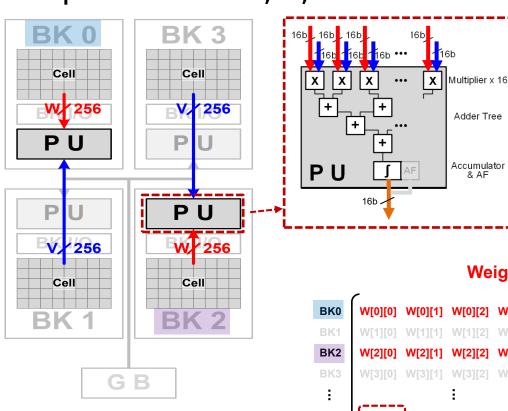
GB

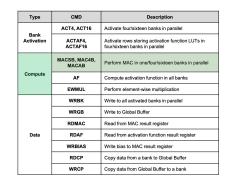


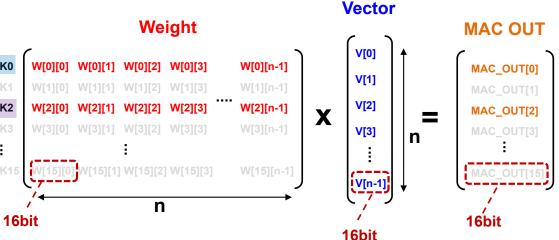


AiM: MAC Operation without Global Buffer

- MAC operation: Weights and vectors from the banks
- Operates with 8, 4, or 1 PU

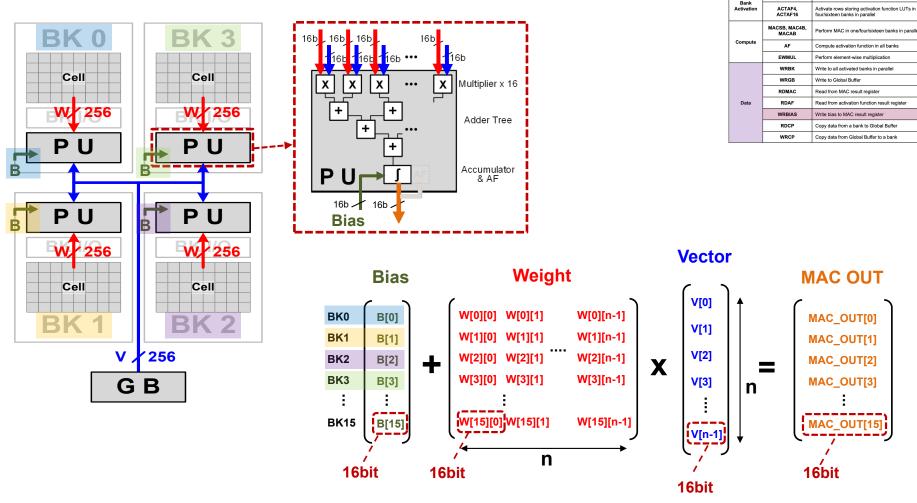






AiM: Write Bias

- Biases can be added to MAC results
 - Different biases in 16 banks at the same time



CMD

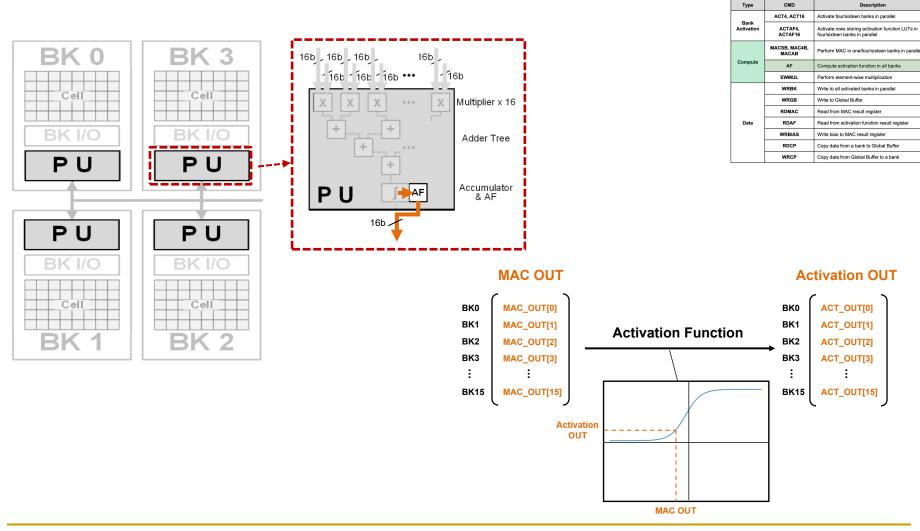
ACT4, ACT16

Description

Activate four/sixteen banks in parallel

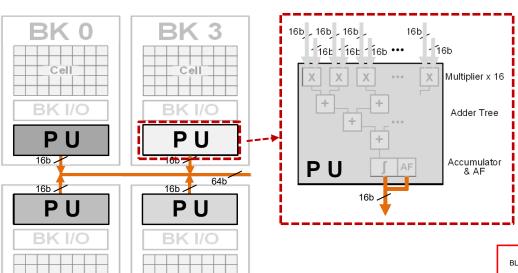
AiM: Activation Function

Activation function (AF): MAC result as input

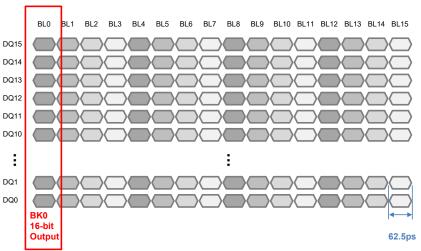


AiM: Read MAC / Read AF

- Read outside DRAM
 - 16 banks x 16 bits = 256 bits



Туре	CMD	Description
ACT4, ACT16		Activate four/sixteen banks in parallel
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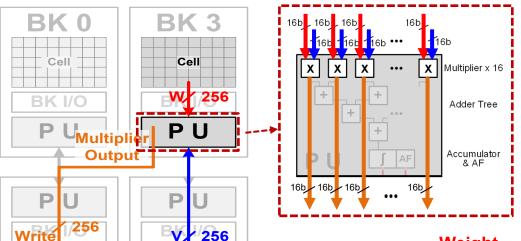


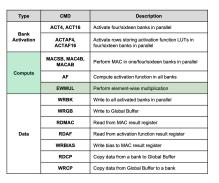
AiM: Element-wise Multiplication

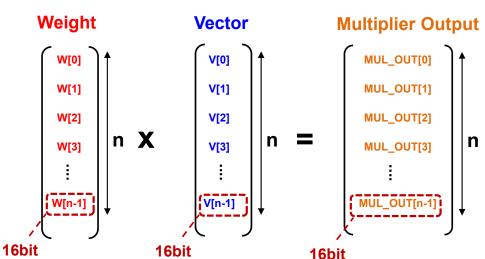
- Multiplies weights and vectors
 - The adder tree is disabled

Cell

Cell



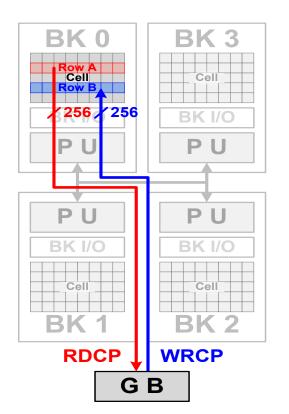


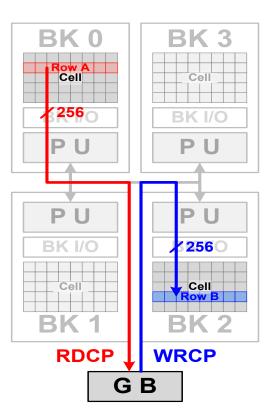


AiM: Copy Operation

- Copy operation using GB as a intermediate buffer
 - It copies 2 KB from one row to another row

Copy to Same Bank Copy to Another Bank

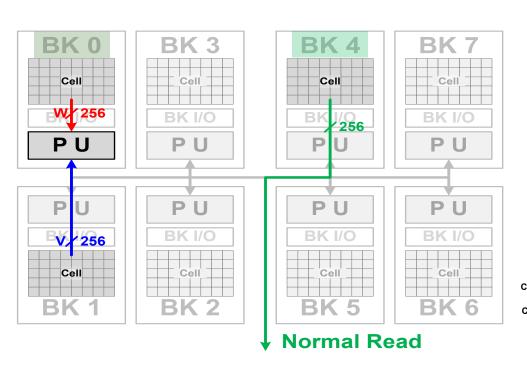




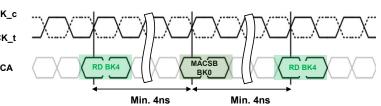
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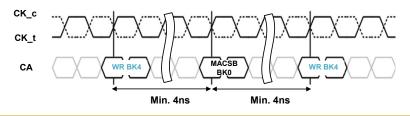
AiM: Simultaneous Computation and Access

Computation can be performed during normal read/write



Type	CMD	Description
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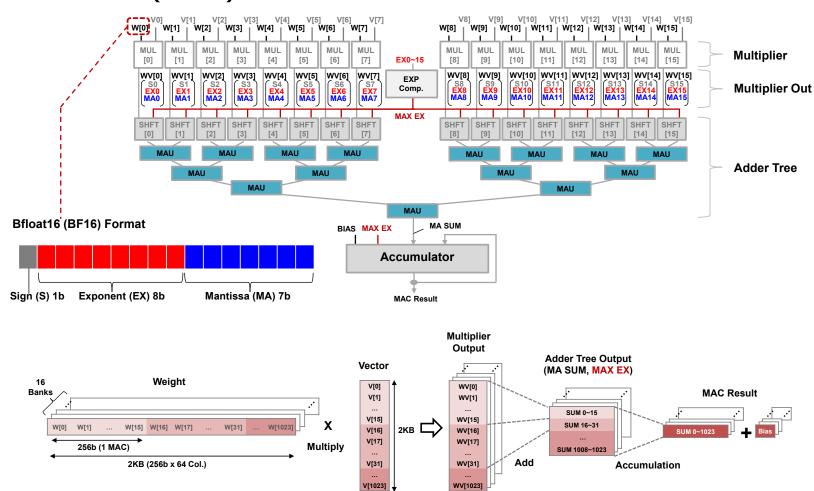




AiM Microarchitecture

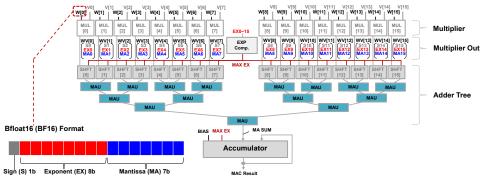
AiM: MAC Circuit

- 16 multipliers, adder tree, and accumulator
 - Bfloat16 (BF16) format

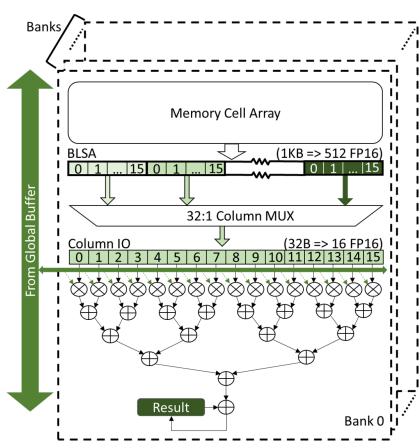


AiM: MAC Circuit: Prior Work (I)

16 multipliers, adder tree, and accumulator

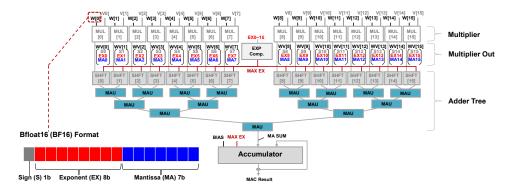


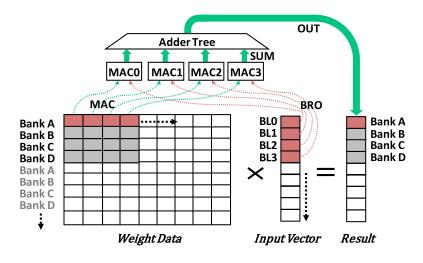
He et al, "Newton: A DRAM-maker's acceleratorin-memory (AiM) architecture for machine learning," MICRO 2020



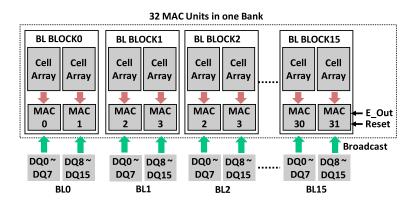
AiM: MAC Circuit: Prior Work (II)

16 multipliers, adder tree, and accumulator

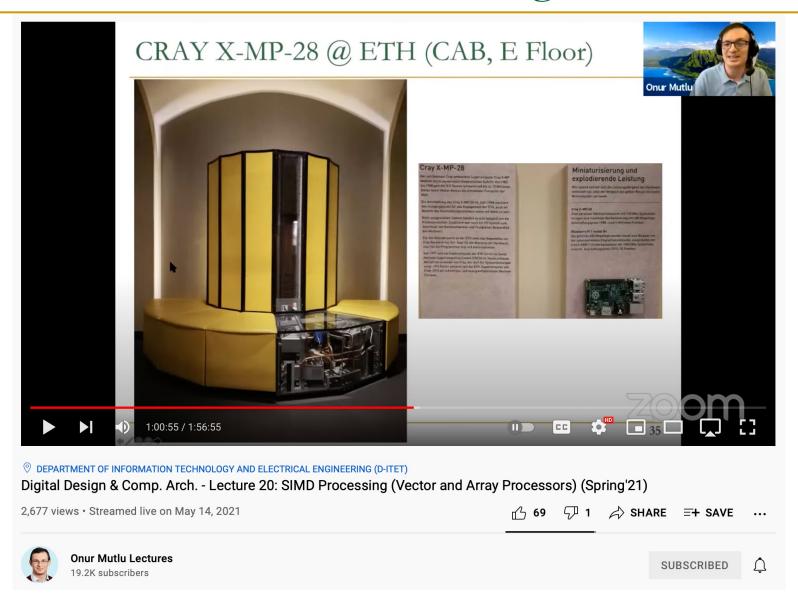




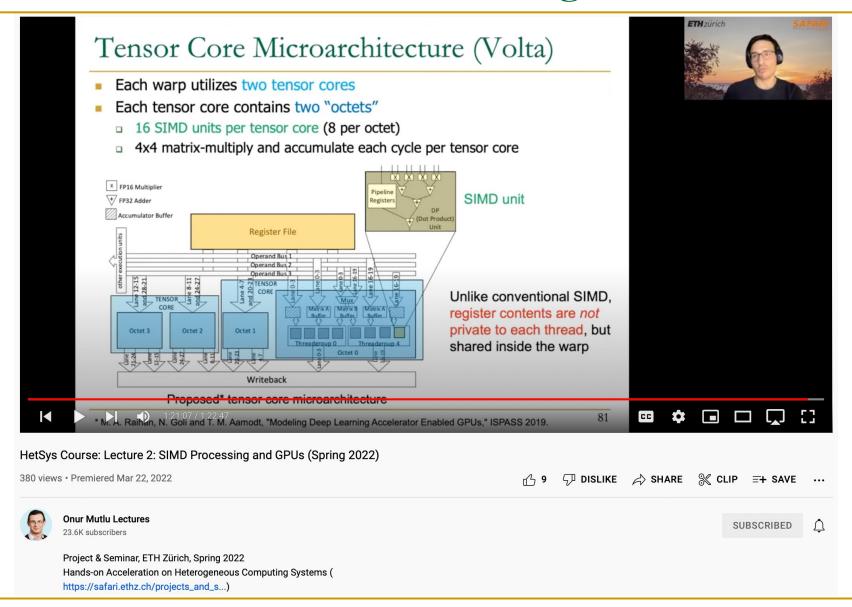
Shin et al, "McDRAM: Low latency and energyefficient matrix computations in DRAM," IEEE TCADICS (2018)



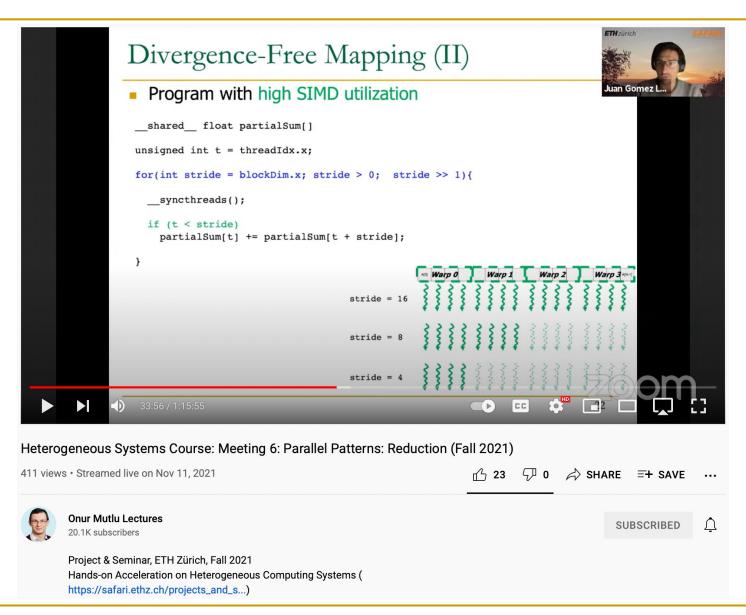
Lecture on SIMD Processing



Lecture on SIMD Processing and GPUs

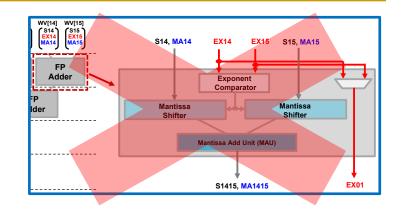


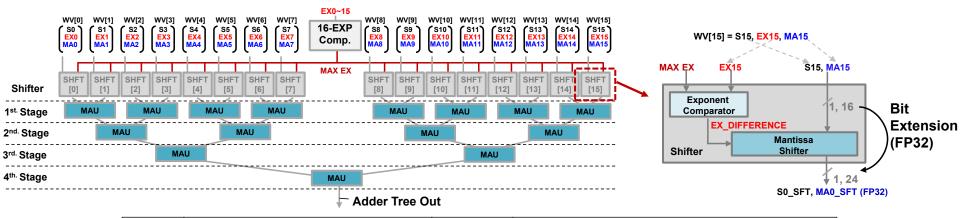
Parallel Reduction on GPU



AiM: Adder Tree: Bank-wide Mantisa Shift (I)

- Bank-wide Mantisa Shift (BWMS)
 - Find MAX EX of 16 EXs
 - Obtain the differences
 - Shift all MAs by the differences
 - Perform MA additions

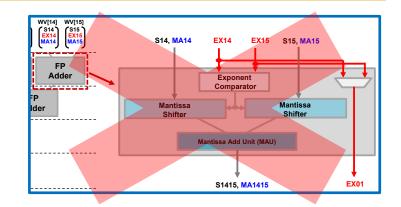


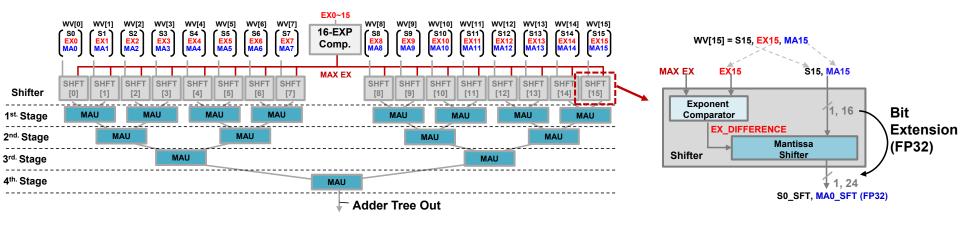


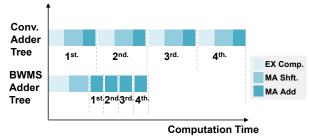
	Before Shifter		Diff w/ May	After Shifter	
MUL OUT	Exponent (EX) (8 bits)	Sign (S), Mantissa (MA) (1, 16 bits)	Diff. w/ Max EX	Exponent (EX) (8 bits)	Sign(S), Mantissa(MA) (1, 24 bits)
WV[0]	00001100	+1.111110011111011	3		+0.00111111001111101100000
WV[1]	00001111	+1.000000011111011	Max EX		+1.00000001111101100000000
WV[2]	00000100	- 1.111110000000000	11	00001111	- 1.111111111111111100000000
I	ı	I	I		i
WV[15]	00001000	+1.000000011111111	7		+0.000000 700000000111111110

AiM: Adder Tree: Bank-wide Mantisa Shift (II)

- Bank-wide Mantisa Shift (BWMS)
 - Find MAX EX of 16 EXs
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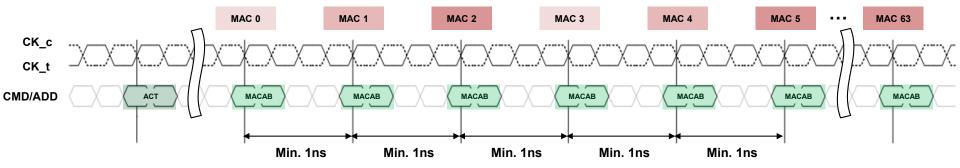




AiM: Accumulation Operation

- Up to 64 MAC commands between ACT
 - 1 MAC every 1ns (t_{CCDS})
 - \bigcirc 64 x 256 bits = 2 KB (row size)

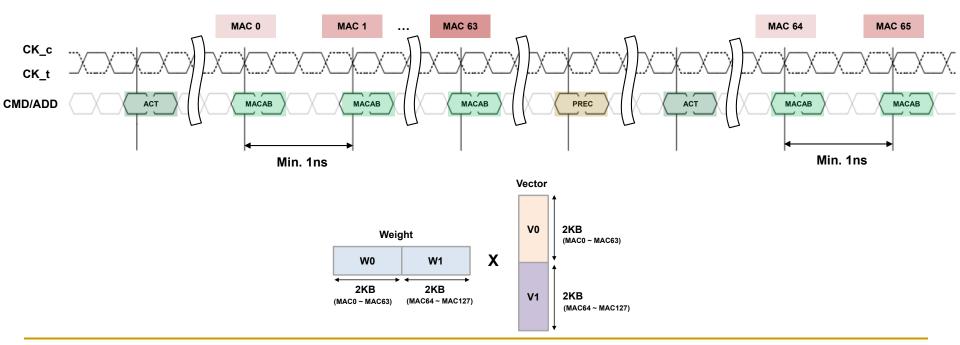
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AiM: Accumulation Operation

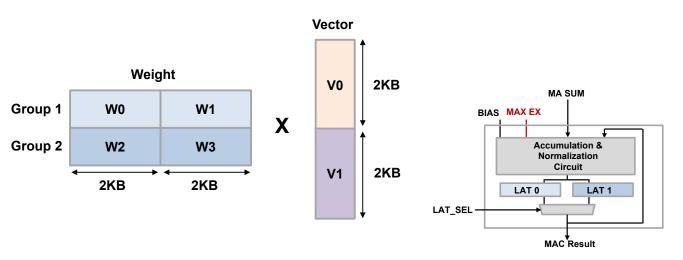
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AiM: Multi-latch Operation

Save writes with selectable latches

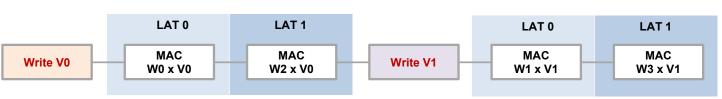


Type	CMD	Description
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Accumulator with Two Selectable Latches Storing MAC Results



Operation Sequence without Multi-Latch

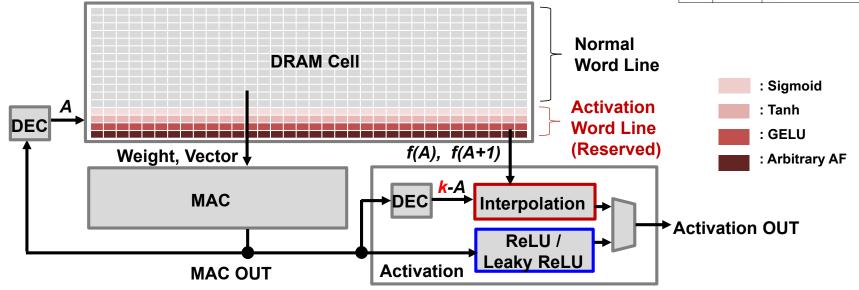


Operation Sequence with Multi-Latch

AiM: Activation Functions (I)

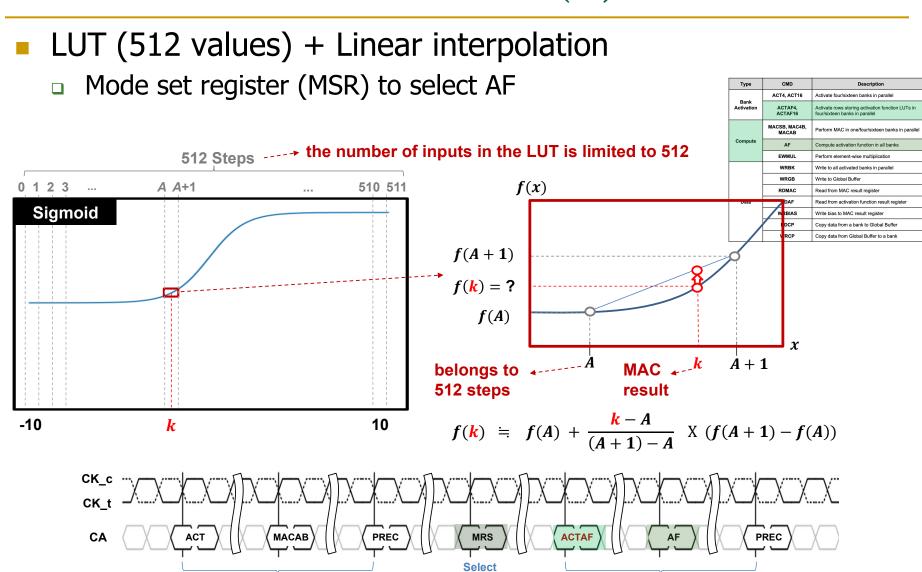
- Two types of activation functions
 - Calculation: ReLU, Leaky ReLU
 - With LUT: Sigmoid, GELU, Tanh, arbitrary AF

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	WRBK	Write to all activated banks in parallel	
	WRGB	Write to Global Buffer	
	RDMAC	Read from MAC result register	
Data	RDAF	Read from activation function result register	
	WRBIAS	Write bias to MAC result register	
	RDCP	Copy data from a bank to Global Buffer	
	WRCP	Copy data from Global Buffer to a bank	
	Bank Activation	AC14, AC116 AC14, AC146 AC1476 AC17476 MACSB, MAC4B, MACAB, MACAB MACAB AF EWMUL WRBK WRGB RDMAC Data RDAF WRBIAS RDCP	



AiM: Activation Functions (II)

MAC



Activation

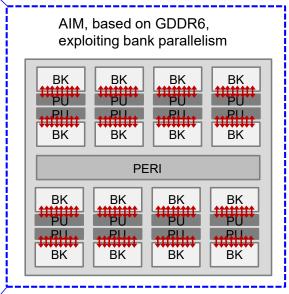
Function

Activation

AiM: Key Feature Summary

Comparison table

	[1]	UPMEM PIM [2]	FIMDRAM [3, 7]	This work
DRAM Type	LPDDR4	DDR4	HBM2	GDDR6
Process	20nm	2x nm	20 nm	1y nm
Memory Density	8GB/chip (8H 8Gb mono die)	8GB/DIMM	6GB/cube (Buffer die + 4H 4Gb core-die with + 4H 8Gb core-die)	8Gb/chip (4Gb DDP)
Data Rate	3.2Gbps	2.4Gbps	2.4Gbps	16Gbps
Bandwidth	25.6GB/s per chip	19.2GB/s per DIMM	307GB/s per cube	64GB/s per chip
# of Processing Unit (PU)	2048 per chip (256 per die)	128 per DIMM (8 per chip)	128 per cube (32 per core-die)	32 per chip (16 per die)
Processing Operation Speed	250MHz	500MHz	300MHz	1GHz
1 PU Throughput	2 GOPS (250MHz x 8byte)	4 GOPS (500MHz x 8byte)	9.6 GFLOPS (300MHz x 32byte)	32 GFLOPS (1GHz x 32byte)
Total Throughput (1 PU Throughput x # of PU)	0.5 TOPS per chip (2 GOPS x 256)	0.5 TOPS per DIMM (4 GOPS x 128)	1.2 TFLOPS per cube (9.6 GFLOPS x 128)	1 TFLOPS per chip (32 GFLOPS x 32)
Operation precision	INT8	INT8	FP16	BF16
Supported Activation Functions	-	-	ReLU	Sigmoid, Tanh, GELU, ReLU, Leaky ReLU and Arbitrary AF



[1] H. Shin, et al., IEEE TCADICS 2018,

[2] F. Devaux, IEEE Hot Chips Symp. 2019,

[3] Y.-C. Kwon et al., ISSCC 2021

Upcoming Lectures

More real-world PIM architectures

Programming PIM systems

More on workload characterization for PIM suitability

PUM architectures and prototypes

P&S Processing-in-Memory

Real-World Processing-in-Memory Architectures: SK Hynix Accelerator-in-Memory

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